## Nonlinear Optical Performance of Pb Doped Se-Te-Bi chalcogenide Thin Films

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**Abstract**—Nonlinear optical properties of chalcogenide glasses have attracted much attention the researchers due to their high transparency in far IR region(upto 22  $\mu$ m), high linear and nonlinear refractive index, good glass forming abilities and low phonon energy. Therefore these materials act as a fundamental material in optical fibers, optical limiting devices, frequency generation etc. The objective of the present study is to find out the nonlinear optical properties of Pb doped Se-Te-Bi chalcogenide thin films. The glassy samples were prepared by well-known melt quench technique. Thermal evaporation technique has been used for the deposition of thin films on the cleaned glass substrate at a pressure of  $10^{-4}$  Pa. The transmission spectra of the thin films in the spectral range 400 - 2500 nm were taken using UV-Vis-NIR spectrophotometer. The transmission spectra of thin film samples represent the fringes due to interference at different wavelengths(Figure 1).



The refractive index is calculated by well-known Swanepoel's method[1]. The linear refractive index (n)increases with increase in Pb composition which is ascribed to the increased polarizability of the larger atomic radius of Pb atoms (Figure 2). Tichy and Ticha[2]model utilized linear refractive index for the analysis of nonlinear refractive index ( $n_2$ ) and is found to be increased 6.9x  $10^{-10}$  esu with the addition of Pb content. The behavior of  $n_2$  with n is shown in Figure. 3 and it is found that  $n_2$  increase linearly withn. The values of nonlinear refractive index of the studied composition are compared with pure silica and found to be 1000 times higher.

## REFERENCES

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